

54F/74F38 **Quad Two-Input NAND Buffer** (Open Collector)

General Description

This device contains four independent gates, each of which performs the logic NAND function. The open-collector outputs require external pull-up resistors for proper logical op-

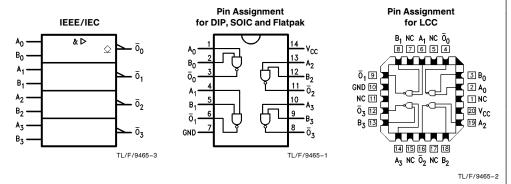
Commercial	Military	Package Number	Package Description
74F38PC		N14E	14-Lead (0.300" Wide) Molded Dual-In-Line
	54F38DM (Note 2)	J14A	14-Lead Ceramic Dual-In-Line
74F38SC (Note 1)		M14A	14-Lead (0.150" Wide) Molded Small Outline, JEDEC
74F38SJ (Note 1)		M14D	14-Lead (0.300" Wide) Molded Small Outline, EIAJ
	54F38FM (Note 2)	W14B	14-Lead Cerpack
	54F38LM (Note 2)	E20A	20-Lead Ceramic Leadless Chip Carrier, Type C

Note 1: Devices also available in 13" reel. Use suffix = SCX and SJX.

Note 2: Military grade device with environmental and burn-in processing. Use suffix = DMQB, FMQB and LMQB.

Logic Symbol

Connection Diagrams



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Unit Loading/Fan Out

		54F/74F				
Pin Names	Description	U.L. HIGH/LOW	Input I _{IH} /I _{IL} Output I _{OH} /I _{OL}			
A _n , B _n	Inputs Outputs	1.0/2.0 OC*/106.6 (80)	20 μA/ – 1.2 mA OC*/64 mA (48 mA)			

^{*}OC = Open Collector

Function Table

Inp	uts	Output		
Α	В	ō		
L	L	Н		
L	Н	Н		
Н	L	Н		
Н	Н	L		

H = HIGH Voltage Level L = LOW Voltage Level

Absolute Maximum Ratings (Note 1)

If Military/Aerospace specified devices are required, please contact the National Semiconductor Sales Office/Distributors for availability and specifications.

Storage Temperature -65°C to $+150^{\circ}\text{C}$ -55°C to +125°C Ambient Temperature under Bias Junction Temperature under Bias -55°C to +175°C Plastic -55°C to +150°C

V_{CC} Pin Potential to

Ground Pin -0.5V to +7.0VInput Voltage (Note 2) -0.5V to +7.0VInput Current (Note 2) $-30\ \text{mA}$ to $+5.0\ \text{mA}$

Voltage Applied to Output in HIGH State (with V_{CC} = 0V)

 $-0.5\mbox{V to V}_{CC} \\ -0.5\mbox{V to } +5.5\mbox{V}$ Standard Output TRI-STATE® Output

Current Applied to Output

in LOW State (Max) twice the rated I_{OL} (mA)

Note 1: Absolute maximum ratings are values beyond which the device may be damaged or have its useful life impaired. Functional operation under these conditions is not implied.

Note 2: Either voltage limit or current limit is sufficient to protect inputs.

Recommended Operating Conditions

Free Air Ambient Temperature

Military -55°C to +125°C 0°C to +70°C Commercial

Supply Voltage

Military +4.5V to +5.5VCommercial +4.5V to +5.5V

DC Electrical Characteristics

Symbol	Parameter		54F/74F			Units	v _{cc}	Conditions	
Symbol			Min	Тур	Max	Onits	VCC	Conditions	
V _{IH}	Input HIGH Voltage		2.0			V		Recognized as a HIGH Signal	
V_{IL}	Input LOW Voltage	Input LOW Voltage			0.8	V		Recognized as a LOW Signal	
V_{CD}	Input Clamp Diode Voltage				-1.2	V	Min	$I_{\text{IN}} = -18 \text{mA}$	
V _{OL}	Output LOW Voltage	54F 10% V _{CC} 74F 10% V _{CC}			0.55 0.55	٧	Min	I _{OL} = 48 mA I _{OL} = 64 mA	
I _{IH}	Input HIGH Current	54F 74F			20.0 5.0	μΑ	Max	$V_{IN} = 2.7V$	
I _{BVI}	Input HIGH Current Breakdown Test	54F 74F			100 7.0	μΑ	Max	V _{IN} = 7.0V	
V _{ID}	Input Leakage Test	74F	4.75			٧	0.0	$I_{ m ID}=1.9~\mu{ m A}$ All Other Pins Grounded	
I _{OD}	Output Leakage Circuit Current	74F			3.75	μΑ	0.0	V _{IOD} = 150 mV All Other Pins Grounded	
I _{IL}	Input LOW Current				-1.2	mA	Max	V _{IN} = 0.5V	
I _{OHC}	Open Collector, Outp OFF Leakage Test	ut			250	μΑ	Min	$V_{OUT} = V_{CC}$	
Icch	Power Supply Curren	t		2.1	7.0	mA	Max	V _O = HIGH	
ICCL	Power Supply Curren	t		26.0	30.0	mA	Max	V _O = LOW	

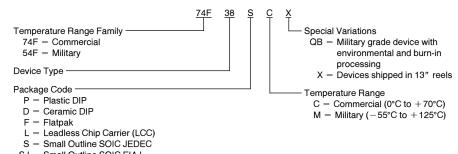
AC Electrical Characteristics

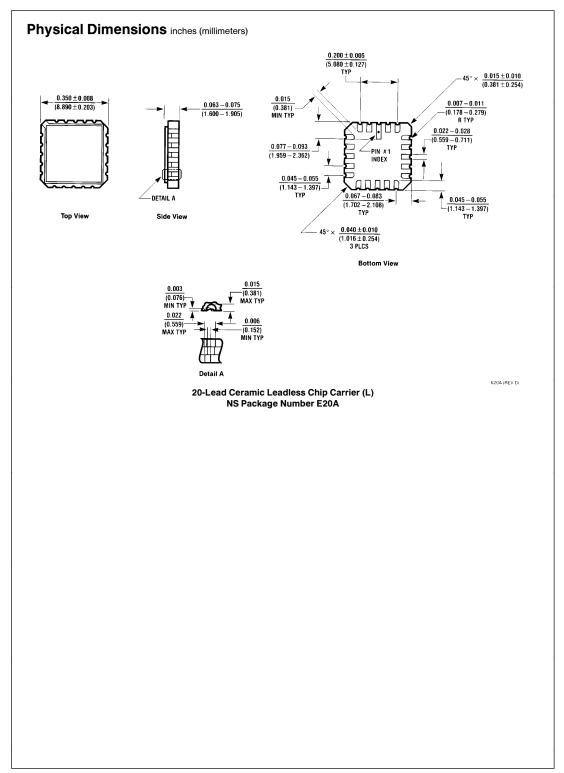
Symbol	Parameter	74F			5-	4F	74F		
		$\begin{aligned} \textbf{T}_{\textbf{A}} &= +25^{\circ}\textbf{C} \\ \textbf{V}_{\textbf{CC}} &= +5.0\textbf{V} \\ \textbf{C}_{\textbf{L}} &= 50~\textbf{pF} \end{aligned}$			$ extsf{T}_{ extsf{A}}, extsf{V}_{ extsf{CC}} = extsf{Mil} \ extsf{C}_{ extsf{L}} = extsf{50 pF}$		$ extsf{T}_{ extsf{A}}, extsf{V}_{ extsf{CC}} = extsf{Com} \ extsf{C}_{ extsf{L}} = extsf{50 pF}$		Units
		Min	Тур	Max	Min	Max	Min	Max	
t _{PLH}	Propagation Delay	6.5	9.7	12.5	6.5	14.5	6.5	13.0	ns
t _{PHL}	A_n , B_n to \overline{O}_n	1.5	2.1	5.0	1.0	5.5	1.5	5.5	113

Ordering Information

SJ = Small Outline SOIC EIAJ

The device number is used to form part of a simplified purchasing code where the package type and temperature range are defined as follows:

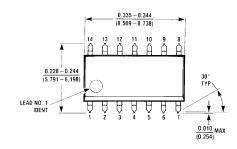




Physical Dimensions inches (millimeters) (Continued) 0.785 (19.939) MAX 14 13 12 11 10 9 8 0.025 (0.635) RAD 1 2 3 4 5 6 7 0.005 (0.127) MIN 0.290-0.320 (7.366-8.128) GLASS SEALANT 0.060 ±0.005 (1.524 ±0.127) 0.180 MA

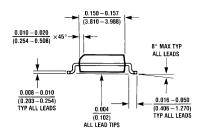
(0.508-1.524) 10° MAX 0.008-0.012 0.310-0.410 0.125-0.200 0.098 (0.457 ±0.076) (2.489) MAX BOTH ENDS (3.175-5.080) 0.100 ±0.010 0.150 (3.81) MIN

14-Lead Ceramic Dual-In-Line Package (D) NS Package Number J14A

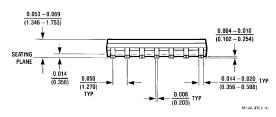


0.220-0.310 (5.588-7.874)

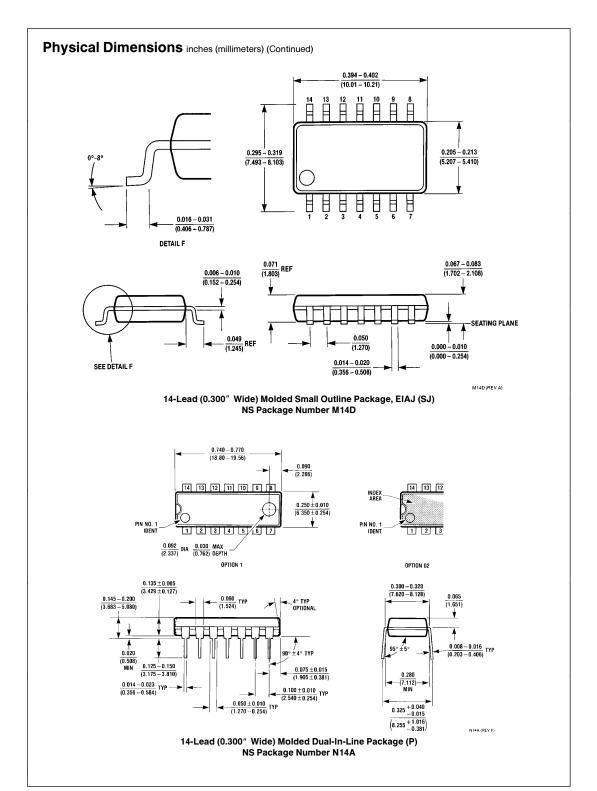
0.200 (5.080) MAX 0.020-0.060



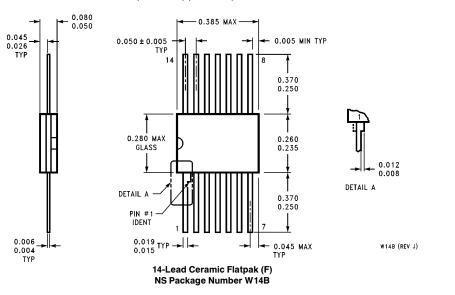
(4.572)



14-Lead (0.150" Wide) Molded Small Outline Package, JEDEC (S) NS Package Number M14A



Physical Dimensions inches (millimeters) (Continued)



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